



20V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C (Note 5)
	175mΩ @ $V_{GS} = 4.5V$	1.30A
20V	240mΩ @ $V_{GS} = 2.5V$	1.11A
	360mΩ @ V _{GS} = 1.8V	0.91A
	500mΩ @ V _{GS} = 1.5V	0.82A

Features

- Footprint of Just 0.6mm² Thirteen Times Smaller Than SOT23
- 0.4mm Profile Ideal for Low Profile Applications
- Low Gate Threshold Voltage
- Fast Switching Speed
- **ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Description

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Mechanical Data

- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.001 grams (Approximate)

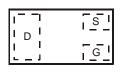
Applications

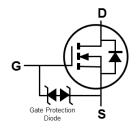
Load Switch

X2-DFN1006-3









Bottom View

Top View

Equivalent Circuit

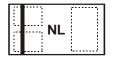
Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DMN2300UFB4-7B	NL	7	8	10,000

- Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 - 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

DMN2300UFB4-7B



Top View Bar Denotes Gate and Source Side

NL = Product Type Marking Code



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 5) V _{GS} = 4.5V	Steady State	$T_A = +25$ °C $T_A = +85$ °C	I _D	1.30 0.96	А
Pulsed Drain Current (Note 6)			I _{DM}	6	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_{D}	500	mW
Thermal Resistance, Junction to Ambient @T _A = +25°C	$R_{\theta JA}$	250	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

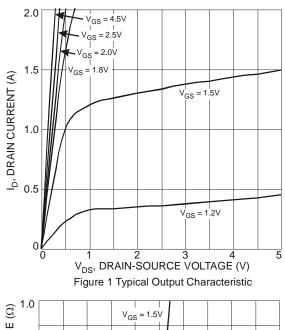
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

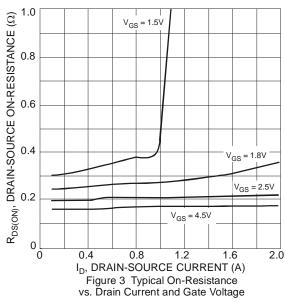
Chavastavistia	Compleal	N4:	T	Max	I Imit	Took Condition	
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	T 51/	00	1	1		lv	
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V$, $I_D = 10\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	1	μA	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	10	μΑ	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	0.45	_	0.95	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
			_	175		$V_{GS} = 4.5V, I_D = 1A$	
Static Drain-Source On-Resistance	D	1	_	240	mO.	$V_{GS} = 2.5V, I_D = 750mA$	
Static Dialii-Source Off-Resistance	R _{DS(ON)}	_	_	360	mΩ	$V_{GS} = 1.8V, I_D = 500mA$	
		-	_	500		$V_{GS} = 1.5V, I_D = 200mA$	
Forward Transfer Admittance	Y _{fs}	40	_	_	mS	$V_{DS} = 3V, I_{D} = 30mA$	
Diode Forward Voltage	V _{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 300mA$	
DYNAMIC CHARACTERISTICS							
Input Capacitance	Ciss	1	67.6		pF	\\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
Output Capacitance	Coss	1	9.7	_	pF	$V_{DS} = 20V, V_{GS} = 0V,$ $V_{DS} = 1.0MHz$	
Reverse Transfer Capacitance	Crss	_	7.5	_	pF		
Gate Resistance	Rg	_	70	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	_	1.6	_	nC	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
Gate-Source Charge	Q _{gs}	_	0.2	_	nC	$V_{GS} = 4.5V, V_{DS} = 15V,$ $I_{D} = 1A$	
Gate-Drain Charge	Q_{gd}	_	0.2	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	3.5	_	ns		
Turn-On Rise Time	t _R	_	2.8	_	ns	$V_{DS} = 10V, I_{D} = 1A$	
Turn-Off Delay Time	t _{D(OFF)}	_	38	_	ns	$V_{GS} = 10V, R_G = 6\Omega$	
Turn-Off Fall Time	t _F	_	13	_	ns		

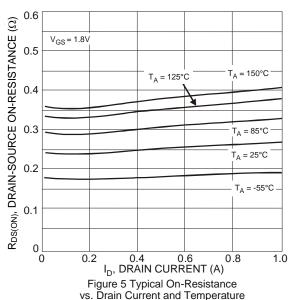
Notes:

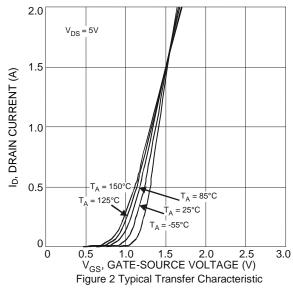
- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
 6. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
 7. Short duration pulse test used to minimize self-heating effect.

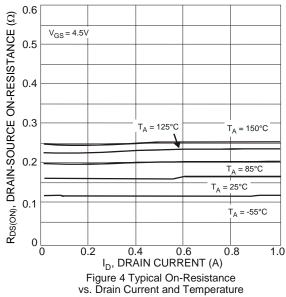














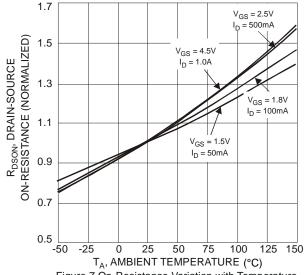


Figure 7 On-Resistance Variation with Temperature

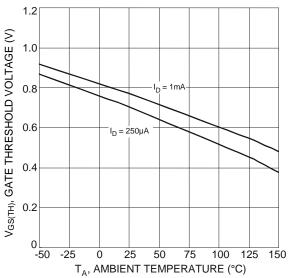
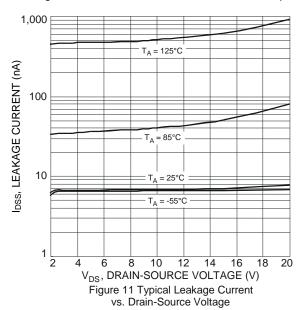


Figure 9 Gate Threshold Variation vs. Ambient Temperature



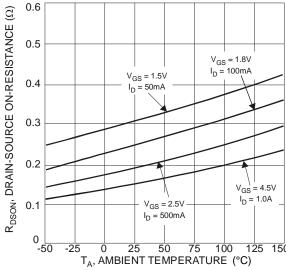
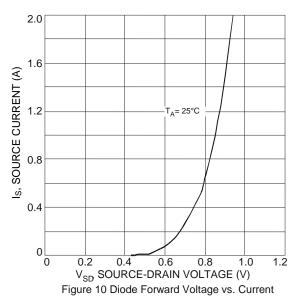


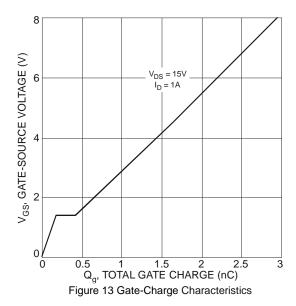
Figure 8 On-Resistance Variation with Temperature

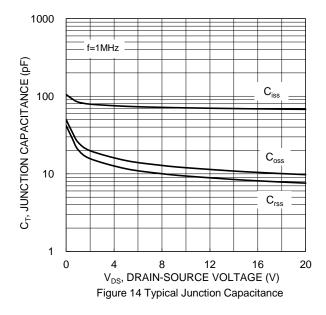


100,000 IDSS, LEAKAGE CURRENT (nA) 10,000 1,000 = 85°C 100 = 25°C _= -55°C 10 1 8 V_{GS}, GATE-SOURCE VOLTAGE (V)

Figure 12 Leakage Current vs. Gate-Source Voltage







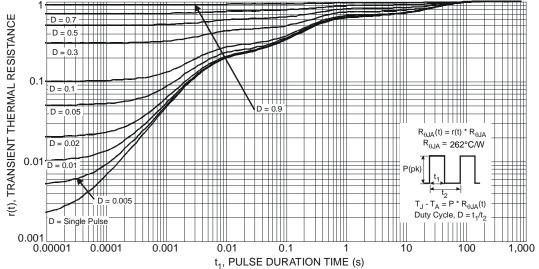


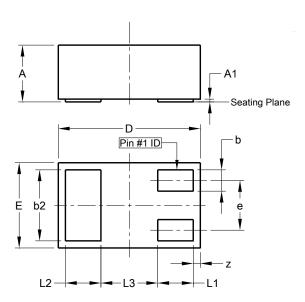
Figure 15 Transient Thermal Response



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1006-3

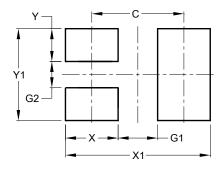


X2-DFN1006-3					
Dim	Min	Max	Тур		
Α	_	0.40	_		
A1	0.00	0.05	0.03		
b	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.05	1.00		
Е	0.55	0.65	0.60		
е	-	-	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3	1	1	0.40		
Z	0.02	0.08	0.05		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1006-3



Dimensions	Value (in mm)		
С	0.70		
G1	0.30		
G2	0.20		
Х	0.40		
X1	1.10		
Y	0.25		
V1	0.70		



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